

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants:	Jack H. Yuan, Eliyahou Harari, Yupin K. Fong and George Samachisa		
Title:	Scalable Self-Aligned Dual Floating Gate Memory Cell Array and Methods of Forming the Array		
Application No.:	Unassigned	Filing Date:	Herewith
Examiner:	Unassigned	Group Art Unit:	Unassigned
Docket No.:	SNDK.257US2	Conf. No.:	Unassigned

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Mail Stop Patent Application  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**INFORMATION DISCLOSURE STATEMENT**

Dear Sir:

Pursuant to 37 C.F.R. §§ 1.56, 1.97 and 1.98, Applicants call the documents listed on the enclosed Form PTO-1449 to the Examiner's attention in this patent application. Copies of the documents listed on the accompanying Form PTO-1449 that are not enclosed were previously submitted in Applications No. 09/925,102, from which this Application claims an earlier effective filing date.

Citation of these documents shall not be construed as (1) an admission that the documents are prior art with respect to the invention or inventions claimed in this application, (2) a representation that a search has been made (other than as indicated by any cited document), or (3) an admission that the cited information is, or is considered to be, material to patentability as defined in § 1.56(b).

This information disclosure statement is submitted under 37 C.F.R. § 1.97(b) and consequently no fee should be required. The Commissioner is authorized, however, to charge

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Attorney Docket No.: SNDK.257US2

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any fee that may be required, or to credit any overpayment, against Deposit Account No. 502664. This form is being submitted in duplicate.

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Respectfully submitted,

  
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Reg. No. 24,486

March 12, 2004  
Date

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U.S. Department of Commerce, Patent and Trademark Office				Atty Docket No.		Serial No.	
				M-11822 US		09/925,102	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Applicant(s)			
(Use several sheets if necessary)				Jack H. Yuan et al.			
<b>COPY</b>				Filing Date		Group	
				August 8, 2001		2185	
U.S. Patent Documents							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA	5,043,940	Aug. 27, 1991	Harari			
	AB	5,070,032	Dec. 3, 1991	Yuan et al.			
	AC	5,095,344	Mar. 10, 1992	Harari			
	AD	5,172,338	Dec. 15, 1992	Mehrotra et al.			
	AE	5,297,148	Mar. 22, 1994	Harari et al.			
	AF	5,313,421	May 17, 1994	Guterman et al.			
	AG	5,315,541	May 24, 1994	Harari et al.			
	AH	5,343,063	Aug. 30, 1994	Yuan et al.			
	AI	5,661,053	Aug. 26, 1997	Yuan			
	AJ	5,712,180	Jan. 27, 1998	Guterman et al.			
	AK	6,103,573	Aug. 15, 2000	Harari et al.			
Foreign Patent Documents							
							Translation
		Document	Date	Country	Class	Subclass	Yes No
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)							
	AL	Aritome, Seiichi, "Advanced Flash Memory Technology and Trends for File Storage Application," IEDM Technical Digest, International Electronic Devices Meeting, IEEE, San Francisco, California, December 10-13, 2000, pp 33.1.1-33.1.4.					
	AM	Takeuchi, Y., et al., "A Self-Aligned STI Process Integration for Low Cost and Highly Reliable 1Gbit Flash Memories," 1998 Symposium on VLSI Technology; Digest of Technical Papers, IEEE, Honolulu, Hawaii, June 9-11, 1998, pp. 102-103.					
	AN	Lee, Jae-Duk, et al., "Effects of Parasitic Capacitance on NAND Flash Memory Cell Operation," Non-Volatile Semiconductor Memory Workshop, IEEE, Monterey, California, August 12-16, 2001, pp. 90-92.					
	AO	Chan, et al., "A True Single-Transistor Oxide-Nitride-Oxide EEPROM Device," <i>IEEE Electron Device Letters</i> , Vol. EDL-8, No. 3, March 1987, pp. 93-95.					
Examiner			Date Considered				
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.							

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U.S. Patent Documents							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AP	6,151,248	Nov. 21, 2000	Harari et al.			
	AQ	6,222,762	Apr. 24, 2001	Guterman et al.			
Foreign Patent Documents							
							Translation
		Document	Date	Country	Class	Subclass	Yes No
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)							
	AR	Nozaki et al., "A 1-Mb EEPROM with MONOS Memory Cell for Semiconductor Disk Application," <i>IEEE Journal of Solid State Circuits</i> , Vol. 26, No. 4, April 1991, pp. 497-501.					
	AS	Eitan et al., "NROM: A Novel Localized Trapping, 2-Bit Nonvolatile Memory Cell," <i>IEEE Electron Device Letters</i> , Vol. 21, No. 11, November 2000, pp. 543-545.					
	AT	DiMaria et al., "Electrically-alterable read-only-memory using Si-rich SiO <sub>2</sub> injectors and a floating polycrystalline silicon storage layer," <i>J. Appl. Phys.</i> 52(7), July 1981, pp. 4825-4842.					
	AU	Hori et al., "A MOSFET with Si-implanted Gate-SiO <sub>2</sub> Insulator for Nonvolatile Memory Applications," <i>IEDM</i> 92, April 1992, pp. 469-472.					
Examiner			Date Considered				
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U.S. Department of Commerce, Patent and Trademark	Atty. Docket No.	Application No.
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	SN DK.257US0	09/925,102
(Use several sheets if necessary)	Applicant(s)	
	Jack H. Yuan et al.	
<b>COPY</b>	Filing Date	Group
	Aug. 8, 2001	2818

## U.S. Patent Documents

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA	5,963,889	10/05/1999	Yamauchi			
	AB	6,048,768	04/11/2000	Ding			
	AC	6,103,573	08/15/2000	Harari			
	AD	6,509,222	01/21/2003	Grossi			
	AE	6,518,618	02/11/2003	Fazio			

## U.S. Published Patent Application Documents

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	AF	02/25025	07/08/2002	Intl. Search Report			

## Foreign Patent Documents

							Translation	
		Document	Date	Country	Class	Subclass	Yes	No
	AG	WO 01/41199	07.06.2001	PCT				
	AH	EP 0 780 902 A1	25.06.1997	EP				
	AI	EP 1 104 023 A1	30.05.2001	EP				

## OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)


Examiner	Date Considered
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# Notice of References Cited

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Application/Control No.

09/925,102

Applicant(s)/Patent Under  
Reexamination  
YUAN ET AL.

Examiner

PHUC T DANG

Art Unit

2818

Page 1 of 1

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-6,406,961 B1	06-2002	Chen	438
	B	US-6,151,248	11-2000	Harari et al.	365
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

## FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

## NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	
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	X	

\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.

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<b>U.S. Patent Documents</b>									
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate		
	AA	6,281,075	Aug. 28, 2001	Yuan et al.					
	AB								
	AC								
	AD								
	AE								
	AF								
	AG								
	AH								
	AI								
	AJ								
	AK								
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							Translation		
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